

Product Overview

NGTB75N60FL2: IGBT, 600V 75A FS2 Solar/UPS

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss.

Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 5 μ s Short-Circuit Capability

Applications

- Solar Inverters
- Uninterruptible Power Supplies (UPS)
- Welding

For more information please contact your local sales support at www.onsemi.com.

Created on: 1/16/2019